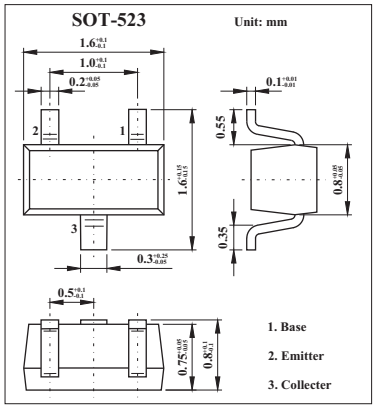
High-frequency Amplifier Transistor

2SC4618



Features

Low collector capacitance.

Low rbb, high gain, and excellent noise characteristics.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	40	V
Collector-emitter voltage	V_{CEO}	25	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	0.15	W
Junction temperature	Tj	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	I_C=50μA	40			V
Collector-emitter breakdown voltage	BV_{CEO}	I_C=1mA	25			V
Emitter-base breakdown voltage	BV_{EBO}	I_E=50μA	5			V
Collector cutoff current	I_{CBO}	V_{CB}=24V			0.5	μA
Emitter cutoff current	I_{EBO}	V_{EB}=3V			0.5	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C/I_B=10mA/1mA			0.3	V
DC current gain	h_{FE}	V_{CE}=6V, I_C=1mA	82		180	
Transition frequency	f_T	V_{CE}=6V, I_E=-1mA, f=100MHz		300		MHz
Output capacitance	C_{ob}	V_{CE}=6V, I_E=0A, f=1MHz		1.3	2.2	pF

Marking

Marking	AN	AP	AQ